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This listing presents the papers in alphabetical order of the first author, subdivided according to the groupings "Solids and Materials" and "Surfaces, Interfaces, and Layer Structures". The author index that follows covers APPLIED PHYSICS A and B, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second column the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The fourth column states the major PACS number so that the topic of the paper can be inferred by consulting the PACS listing on the left page.

## SOLIDS and MATERIALS


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Temperature dependence of slow-positron production and of positronium formation on untreated surfaces.
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Surface polarization effect on positron backdiffusion from dielectrics.
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A model for the high-$T_c$ superconductivity based on electron hopping.
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## SURFACES, INTERFACES, and LAYER STRUCTURES


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